

CLAIM AMENDMENTS

Please cancel claims 8-26 without prejudice or disclaimer.

1. (Original) A method, comprising:
 - disposing two rectangular diffusions of P (+) material in an n-well formed in a p-substrate using a complementary metal oxide semiconductor (CMOS) process;
 - disposing a polycide gate between the two rectangular diffusions of P (+) material;
 - disposing a pair of inductors on the substrate; and
 - coupling the two rectangular diffusions of P (+) material and the pair of inductors in a voltage-controlled oscillator (VCO) configuration.
2. (Original) The method of claim 1 wherein disposing two rectangular diffusions of P (+) material in an n-well formed in a p-substrate using the CMOS process comprises disposing two rectangular diffusions of P (+) material in an n-well formed in an epitaxial substrate using the CMOS process.
3. (Original) The method of claim 1 wherein disposing two rectangular diffusions of P (+) material in an n-well formed in a p-substrate using the CMOS process comprises disposing two rectangular diffusions of P (+) material in an n-well formed in a non-epitaxial substrate using the CMOS process.
4. (Original) The method of claim 3 wherein disposing two rectangular diffusions of P (+) material in an n-well formed in a p-substrate using the CMOS process comprises disposing two rectangular diffusions of P (+) material in an n-well diffused in a p-substrate using the CMOS process.

5. (Original) The method of claim 1 wherein disposing two rectangular diffusions of P (+) material in an n-well formed in a p-substrate using the CMOS process comprises building a metal oxide structure on top of the n-well.
6. (Original) The method of claim 1 further comprising defining the spacing between the two rectangular diffusions of P (+) material using a lightly doped drain (LDD) structure .
7. (Original) The method of claim 1 further comprising defining the spacing between the two rectangular diffusions of P (+) material using halo implantation.

Claims 8-26. (Canceled)